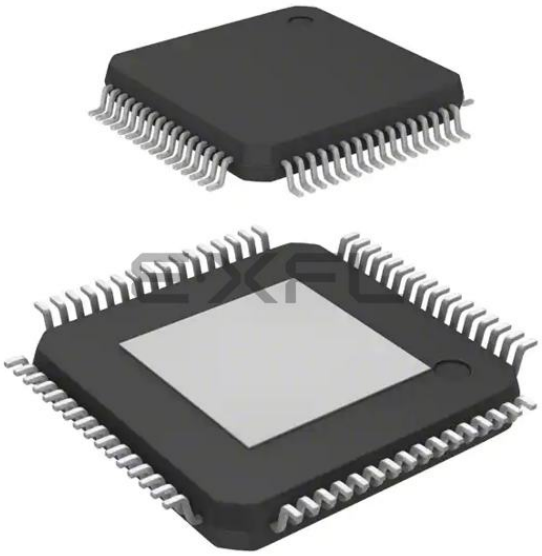
Infineon Technologies - XMC4104F64K128BAXQMA1 Datasheet



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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	80MHz
Connectivity	CANbus, I²C, LINbus, SPI, UART/USART, USB
Peripherals	DMA, I²S, LED, POR, PWM, WDT
Number of I/O	35
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	20K x 8
Voltage - Supply (Vcc/Vdd)	3.13V ~ 3.63V
Data Converters	A/D 10x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP Exposed Pad
Supplier Device Package	PG-LQFP-64-19
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/xmc4104f64k128baxqma1

Table 11 Package Pin Mapping (cont'd)

Function	LQFP-64 TQFP-64	VQFN-48	Pad Type	Notes
P14.9	23	19	AN/DAC/DIG_IN	
P14.14	14	-	AN/DIG_IN	
USB_DP	7	4	special	
USB_DM	6	3	special	
HIB_IO_0	10	7	A1 special	At the first power-up and with every reset of the hibernate domain this pin is configured as open-drain output and drives "0". As output the medium driver mode is active.
TCK	45	34	A1	Weak pull-down active.
TMS	44	33	A1+	Weak pull-up active. As output the strong-soft driver mode is active.
$\overline{\text{PORST}}$	43	32	special	Strong pull-down controlled by EVR. Weak pull-up active while strong pull-down is not active.
XTAL1	39	29	clock_IN	
XTAL2	40	30	clock_O	
RTC_XTAL1	11	8	clock_IN	
RTC_XTAL2	12	9	clock_O	
VBAT	13	10	Power	When VDDP is supplied VBAT has to be supplied as well.
VDDA/VAREF	22	18	AN_Power/AN_ Ref	Shared analog supply and reference voltage pin.
VSSA/VAGND	21	17	AN_Power/AN_ Ref	Shared analog supply and reference ground pin.
VDDC	9	6	Power	
VDDC	42	31	Power	
VDDP	8	5	Power	
VDDP	38	28	Power	
VDDP	56	41	Power	
VSS	37	27	Power	

The XMC4[12]00 has a common ground concept, all V_{SS}, V_{SSA} and V_{SSO} pins share the same ground potential. In packages with an exposed die pad it must be connected to the common ground as well.

There are no dedicated connections for the analog reference V_{AREF} and V_{AGND}. Instead, they share the same pins as the analog supply pins V_{DDA} and V_{SSA}.Some analog channels can optionally serve as “Alternate Reference”; further details on this operating mode are described in the Reference Manual.

When V_{DDP} is supplied, V_{BAT} must be supplied as well. If no other supply source (e.g. battery) is connected to V_{BAT}, the V_{BAT} pin can also be connected directly to V_{DDP}.

3 Electrical Parameters

3.1 General Parameters

3.1.1 Parameter Interpretation

The parameters listed in this section partly represent the characteristics of the XMC4[12]00 and partly its requirements on the system. To aid interpreting the parameters easily when evaluating them for a design, they are marked with an two-letter abbreviation in column “Symbol”:

- **CC**
  Such parameters indicate **C**ontroller **C**haracteristics, which are a distinctive feature of the XMC4[12]00 and must be regarded for system design.
- **SR**
  Such parameters indicate **S**ystem **R**equirements, which must be provided by the application system in which the XMC4[12]00 is designed in.

3.1.2 Absolute Maximum Ratings

Stresses above the values listed under “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions may affect device reliability.

Table 14 Absolute Maximum Rating Parameters

Parameter	Symbol		Values			Unit	Note / Test Condition
			Min.	Typ.	Max.		
Storage temperature	T_{ST}	SR	-65	–	150	°C	–
Junction temperature	T_J	SR	-40	–	150	°C	–
Voltage at 3.3 V power supply pins with respect to V_{SS}	V_{DDP}	SR	–	–	4.3	V	–
Voltage on any Class A and dedicated input pin with respect to V_{SS}	V_{IN}	SR	-1.0	–	V_{DDP} + 1.0 or max. 4.3	V	whichever is lower
Voltage on any analog input pin with respect to V_{AGND}	V_{AIN} V_{AREF}	SR	-1.0	–	V_{DDP} + 1.0 or max. 4.3	V	whichever is lower
Input current on any pin during overload condition	I_{IN}	SR	-10	–	+10	mA	
Absolute maximum sum of all input circuit currents for one port group during overload condition[1)]	ΣI_{IN}	SR	-25	–	+25	mA	
Absolute maximum sum of all input circuit currents during overload condition	ΣI_{IN}	SR	-100	–	+100	mA	

1) The port groups are defined in **Table 18**.

3.2 DC Parameters

3.2.1 Input/Output Pins

The digital input stage of the shared analog/digital input pins is identical to the input stage of the standard digital input/output pins.
The pull-up characteristics (I_{PUH}) and the input high and low voltage levels (V_{IH} and V_{IL}) of the $\overline{\text{PORST}}$ pin are identical to the respective values of the standard digital input/output pins.

Table 21 Standard Pad Parameters

Parameter	Symbol	Values		Unit	Note / Test Condition
		Min.	Max.		
Pin capacitance (digital inputs/outputs)	C_{IO} CC	–	10	pF	
Pull-down current	$\lvert I_{PDL}\rvert$ SR	150	–	µA	1) $V_{IN} \geq 0.6 \times V_{DDP}$
		–	10	µA	2) $V_{IN} \leq 0.36 \times V_{DDP}$
Pull-up current	$\lvert I_{PUH}\rvert$ SR	–	10	µA	2) $V_{IN} \geq 0.6 \times V_{DDP}$
		100	–	µA	1) $V_{IN} \leq 0.36 \times V_{DDP}$
Input Hysteresis for pads of all A classes[3]	$HYSA$ CC	$0.1 \times V_{DDP}$	–	V	
$\overline{\text{PORST}}$ spike filter always blocked pulse duration	t_{SF1} CC	–	10	ns	
$\overline{\text{PORST}}$ spike filter pass-through pulse duration	t_{SF2} CC	100	–	ns	
$\overline{\text{PORST}}$ pull-down current	$\lvert I_{PPD}\rvert$ CC	13	–	mA	$V_i = 1.0$ V

1) Current required to override the pull device with the opposite logic level (“force current”).
With active pull device, at load currents between force and keep current the input state is undefined.

2) Load current at which the pull device still maintains the valid logic level (“keep current”).
With active pull device, at load currents between force and keep current the input state is undefined.

3) Hysteresis is implemented to avoid metastable states and switching due to internal ground bounce. It can not be guaranteed that it suppresses switching due to external system noise.

Table 23 Standard Pads Class_A1+

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.		Max.		
Output high voltage, POD[1] = weak	V_{OHA1+} CC	V_{DDP} - 0.4		–	V	$I_{OH} \geq$ -400 µA
		2.4		–	V	$I_{OH} \geq$ -500 µA
Output high voltage, POD[1] = medium		V_{DDP} - 0.4		–	V	$I_{OH} \geq$ -1.4 mA
		2.4		–	V	$I_{OH} \geq$ -2 mA
Output high voltage, POD[1] = strong		V_{DDP} - 0.4		–	V	$I_{OH} \geq$ -1.4 mA
		2.4		–	V	$I_{OH} \geq$ -2 mA
Output low voltage	V_{OLA1+} CC	–		0.4	V	$I_{OL} \leq$ 500 µA; POD[1] = weak
		–		0.4	V	$I_{OL} \leq$ 2 mA; POD[1] = medium
		–		0.4	V	$I_{OL} \leq$ 2 mA; POD[1] = strong
Fall time	t_{FA1+} CC	–		150	ns	C_L = 20 pF; POD[1] = weak
		–		50	ns	C_L = 50 pF; POD[1] = medium
		–		28	ns	C_L = 50 pF; POD[1] = strong; edge = slow
		–		16	ns	C_L = 50 pF; POD[1] = strong; edge = soft;
Rise time	t_{RA1+} CC	–		150	ns	C_L = 20 pF; POD[1] = weak
		–		50	ns	C_L = 50 pF; POD[1] = medium
		–		28	ns	C_L = 50 pF; POD[1] = strong; edge = slow
		–		16	ns	C_L = 50 pF; POD[1] = strong; edge = soft

1) POD = Pin Out Driver

9) The resulting current for a conversion can be calculated with $I_{AREF} = Q_{CONV} / t_c$.
The fastest 12-bit post-calibrated conversion of t_c = 566 ns results in a typical average current of I_{AREF} = 53 µA.

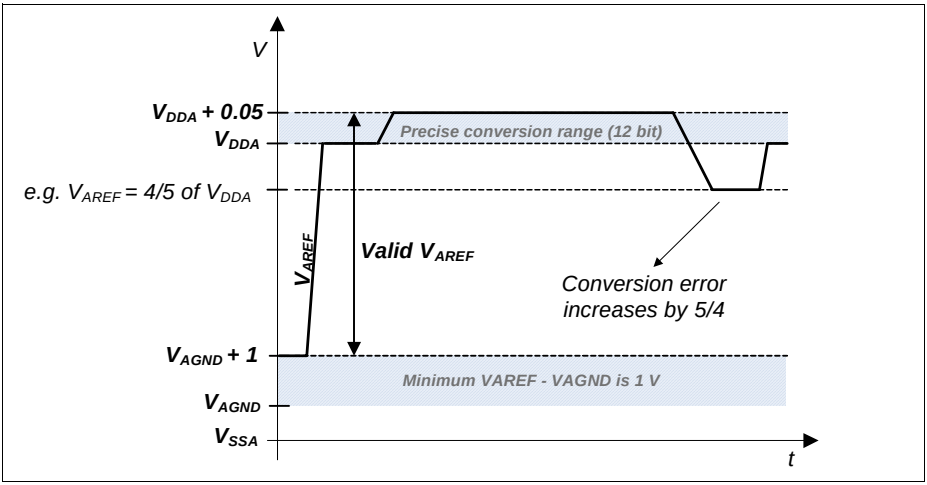

Figure 12 VADC Reference Voltage Range

3.2.3 Digital to Analog Converters (DACx)

Note: These parameters are not subject to production test, but verified by design and/or characterization.

Table 27 DAC Parameters (Operating Conditions apply)

Parameter	Symbol		Values			Unit	Note / Test Condition
			Min.	Typ.	Max.		
RMS supply current	I_{DD}	CC	–	2.5	4	mA	per active DAC channel, without load currents of DAC outputs
Resolution	RES	CC	–	12	–	Bit	
Update rate	f_{URATE_A}	CC	–		2	Msample/s	data rate, where DAC can follow 64 LSB code jumps to ± 1LSB accuracy
Update rate	f_{URATE_F}	CC	–		5	Msample/s	data rate, where DAC can follow 64 LSB code jumps to ± 4 LSB accuracy
Settling time	t_{SETTLE}	CC	–	1	2	µs	at full scale jump, output voltage reaches target value ± 20 LSB
Slew rate	SR	CC	2	5	–	V/µs	
Minimum output voltage	V_{OUT_MIN}	CC	–	0.3	–	V	code value unsigned: 000_H; signed: 800_H
Maximum output voltage	V_{OUT_MAX}	CC	–	2.5	–	V	code value unsigned: FFF_H; signed: $7FF_H$
Integral non-linearity[1)]	INL	CC	-5.5	±2.5	5.5	LSB	$R_L \geq 5$ kOhm, $C_L \leq 50$ pF
Differential non-linearity	DNL	CC	-2	±1	2	LSB	$R_L \geq 5$ kOhm, $C_L \leq 50$ pF

3.2.4 Out-of-Range Comparator (ORC)

The Out-of-Range Comparator (ORC) triggers on analog input voltages (V_{AIN}) above the analog reference[1] (V_{AREF}) on selected input pins (GxORCy) and generates a service request trigger (GxORCOUTy).

Note: These parameters are not subject to production test, but verified by design and/or characterization.

The parameters in **Table 28** apply for the maximum reference voltage $V_{AREF} = V_{DDA} + 50$ mV.

Table 28 ORC Parameters (Operating Conditions apply)

Parameter	Symbol		Values			Unit	Note / Test Condition
			Min.	Typ.	Max.		
DC Switching Level	V_{ODC}	CC	100	125	200	mV	Ax-marking devices $V_{AIN} \geq V_{AREF} + V_{ODC}$
Hysteresis	V_{OHYS}	CC	50	–	V_{ODC}	mV	
Detection Delay of a persistent Overvoltage	t_{ODD}	CC	55	–	450	ns	Ax-marking devices $V_{AIN} \geq V_{AREF} + 200$ mV
			45	–	105	ns	$V_{AIN} \geq V_{AREF} + 400$ mV
Always detected Overvoltage Pulse	t_{OPDD}	CC	440	–	–	ns	Ax-marking devices $V_{AIN} \geq V_{AREF} + 200$ mV
			90	–	–	ns	$V_{AIN} \geq V_{AREF} + 400$ mV
Never detected Overvoltage Pulse	t_{OPDN}	CC	–	–	49	ns	Ax-marking devices $V_{AIN} \geq V_{AREF} + 200$ mV
			–	–	30	ns	$V_{AIN} \geq V_{AREF} + 400$ mV
Release Delay	t_{ORD}	CC	65	–	105	ns	$V_{AIN} \leq V_{AREF}$
Enable Delay	t_{OED}	CC	–	100	200	ns	

1) Always the standard VADC reference, alternate references do not apply to the ORC.

Table 38 Power Supply Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Sleep supply current[3] Peripherals enabled Frequency: f_{CPU} / f_{PERIPH} / f_{CCU} in MHz	I_{DDPS} CC	–	76	–	mA	80 / 80 / 80
		–	73	–		80 / 40 / 40
		–	70	–		40 / 40 / 80
		–	56	–		24 / 24 / 24
		–	47	–		1 / 1 / 1
f_{CPU} / f_{PERIPH} / f_{CCU} in kHz		–	46	–		100 / 100 / 100
Sleep supply current[4] Peripherals disabled Frequency: f_{CPU} / f_{PERIPH} / f_{CCU} in MHz	I_{DDPS} CC	–	59	–	mA	80 / 80 / 80
		–	58	–		80 / 40 / 40
		–	57	–		40 / 40 / 80
		–	51	–		24 / 24 / 24
		–	46	–		1 / 1 / 1
f_{CPU} / f_{PERIPH} / f_{CCU} in kHz		–	46	–		100 / 100 / 100
Deep Sleep supply current[5] Flash in Sleep mode Frequency: f_{CPU} / f_{PERIPH} / f_{CCU} in MHz	I_{DDPD} CC	–	6.9	–	mA	24 / 24 / 24
		–	4.3	–		4 / 4 / 4
		–	3.8	–		1 / 1 / 1
f_{CPU} / f_{PERIPH} / f_{CCU} in kHz		–	4.5	–		100 / 100 / 100 [6]
Hibernate supply current RTC on[7]	I_{DDPH} CC	–	10.8	–	µA	V_{BAT} = 3.3 V
		–	8.0	–		V_{BAT} = 2.4 V
		–	6.8	–		V_{BAT} = 2.0 V
Hibernate supply current RTC off[8]	I_{DDPH} CC	–	10.3	–	µA	V_{BAT} = 3.3 V
		–	7.5	–		V_{BAT} = 2.4 V
		–	6.3	–		V_{BAT} = 2.0 V
Worst case active supply current[9]	I_{DDPA} CC	–	–	140 [10]	mA	V_{DDP} = 3.6 V, T_J = 150 °C
V_{DDA} power supply current	I_{DDA} CC	–	–	–[11]	mA	
I_{DDP} current at $\overline{\text{PORST}}$ Low	I_{DDP_PORST} CC	–	–	24	mA	V_{DDP} = 3.6 V, T_J = 150 °C

Table 38 Power Supply Parameters

Parameter	Symbol		Values			Unit	Note / Test Condition
			Min.	Typ.	Max.		
Power Dissipation	P_{DISS}	CC	–	–	1	W	V_{DDP} = 3.6 V, T_J = 150 °C
Wake-up time from Sleep to Active mode	t_{SSA}	CC	–	6	–	cycles	
Wake-up time from Deep Sleep to Active mode			–	–	–	ms	Defined by the wake-up of the Flash module, see **Section 3.2.11**
Wake-up time from Hibernate mode			–	–	–	ms	Wake-up via power-on reset event, see **Section 3.3.2**

1) CPU executing code from Flash, all peripherals idle.
2) CPU executing code from Flash. USB and CCU clock off.
3) CPU in sleep, all peripherals idle, Flash in Active mode.
4) CPU in sleep, Flash in Active mode.
5) CPU in sleep, peripherals disabled, after wake-up code execution from RAM.
6) To wake-up the Flash from its Sleep mode, $f_{CPU} \geq 1$ MHz is required.
7) OSC_ULP operating with external crystal on RTC_XTAL
8) OSC_ULP off, Hibernate domain operating with OSC_SI clock
9) Test Power Loop: f_{SYS} = 80 MHz, CPU executing benchmark code from Flash, all CCUs in 100kHz timer mode, all ADC groups in continuous conversion mode, USICs as SPI in internal loop-back mode, CAN in 500kHz internal loop-back mode, interrupt triggered DMA block transfers to parity protected RAMs and FCE, DTS measurements and FPU calculations.
   The power consumption of each customer application will most probably be lower than this value, but must be evaluated separately.
10) I_{DDP} decreases typically by 3.5 mA when f_{SYS} decreases by 10 MHz, at constant T_J
11) Sum of currents of all active converters (ADC and DAC)

Table 40 Flash Memory Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Data Retention Time, User Configuration Block (UCB)[3)4)]	t_{RTU} CC	20	–	–	years	Max. 4 erase/program cycles per UCB
Endurance on 64 Kbyte Physical Sector PS4	N_{EPS4} CC	10000	–	–	cycles	BA-marking devices only! Cycling distributed over life time[5)]

1) In case the Program Verify feature detects weak bits, these bits will be programmed once more. The reprogramming takes an additional time of 5.5 ms.

2) The following formula applies to the wait state configuration: FCON.WSPFLASH × (1 / f_{CPU}) ≥ t_a.

3) Storage and inactive time included.

4) Values given are valid for an average weighted junction temperature of T_J = 110°C.

5) Only valid with robust EEPROM emulation algorithm, equally cycling the logical sectors. For more details see the Reference Manual.

3.3.2 Power-Up and Supply Monitoring

$\overline{\text{PORST}}$ is always asserted when V_{DDP} and/or V_{DDC} violate the respective thresholds.

Note: These parameters are not subject to production test, but verified by design and/or characterization.

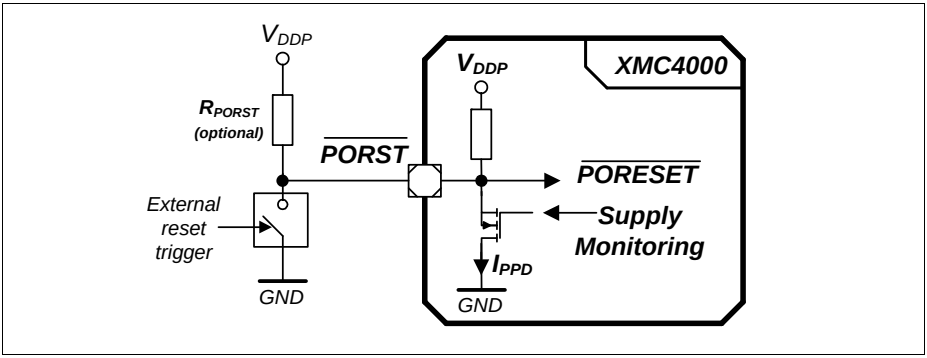

Figure 26 $\overline{\text{PORST}}$ Circuit

Table 41 Supply Monitoring Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Digital supply voltage reset threshold	V_{POR} CC	2.79[1]	–	3.05[2]	V	[3]
Core supply voltage reset threshold	V_{PV} CC	–	–	1.17	V	
V_{DDP} voltage to ensure defined pad states	V_{DDPPA} CC	–	1.0	–	V	
$\overline{\text{PORST}}$ rise time	t_{PR} SR	–	–	2	µs	
Startup time from power-on reset with code execution from Flash	t_{SSW} CC	–	2.5	3.5	ms	Time to the first user code instruction
V_{DDC} ramp up time	t_{VCR} CC	–	550	–	µs	Ramp up after power-on or after a reset triggered by a violation of V_{POR} or V_{PV}

1) Minimum threshold for reset assertion.

Table 42 Power Sequencing Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Positive Load Step Current	ΔI_{PLS} SR	-	–	50	mA	Load increase on V_{DDP} $\Delta t \leq 10$ ns
Negative Load Step Current	ΔI_{NLS} SR	-	–	150	mA	Load decrease on V_{DDP} $\Delta t \leq 10$ ns
V_{DDC} Voltage Over- / Undershoot from Load Step	ΔV_{LS} CC	-	–	±100	mV	For maximum positive or negative load step
Positive Load Step Settling Time	t_{PLSS} SR	50	–	-	µs	
Negative Load Step Settling Time	t_{NLSS} SR	100	–	-	µs	
External Buffer Capacitor on V_{DDC}	C_{EXT} SR	3	4.7	6	µF	In addition C = 100 nF capacitor on each V_{DDC} pin

Positive Load Step Examples

System assumptions:
$f_{CPU} = f_{SYS}$, target frequency f_{CPU} = 80 MHz, main PLL f_{VCO} = 480 MHz, stepping done by K2 divider, t_{PLSS} between individual steps:

24 MHz - 48 MHz - 80 MHz (K2 steps 20 - 10 - 6)
24 MHz - 60 MHz - 80 MHz (K2 steps 20 - 8 - 6)

3.3.4 Phase Locked Loop (PLL) Characteristics

Main and USB PLL

Table 43 PLL Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Accumulated Jitter	D_P CC	–	–	±5	ns	accumulated over 300 cycles f_{SYS} = 80 MHz
Duty Cycle[1)]	D_{DC} CC	46	50	54	%	Low pulse to total period, assuming an ideal input clock source
PLL base frequency	$f_{PLLBASE}$ CC	30	–	140	MHz	
VCO input frequency	f_{REF} CC	4	–	16	MHz	
VCO frequency range	f_{VCO} CC	260	–	520	MHz	
PLL lock-in time	t_L CC	–	–	400	µs	

1) 50% for even K2 divider values, 50±(10/K2) for odd K2 divider values.

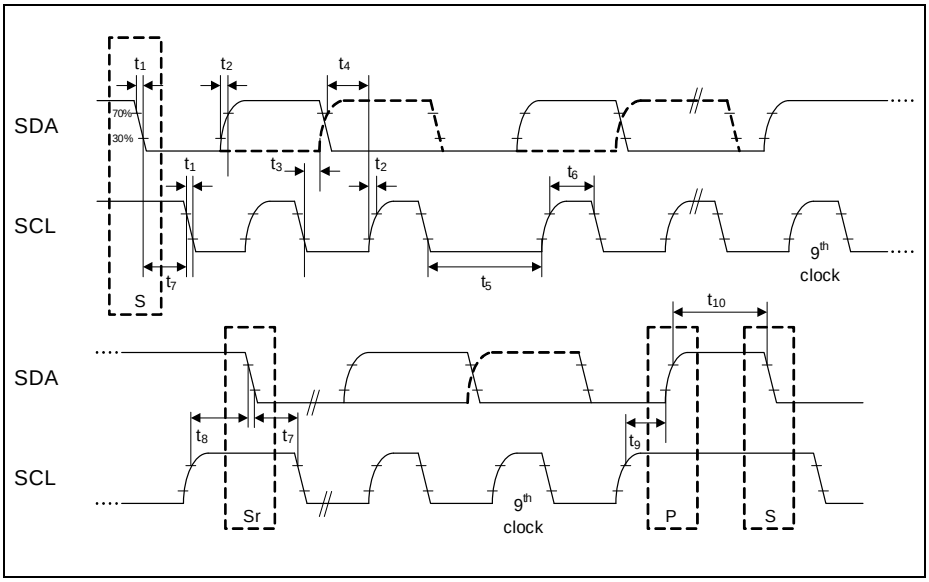

Figure 32 USIC IIC Stand and Fast Mode Timing

3.3.8.3 Inter-IC Sound (IIS) Interface Timing

The following parameters are applicable for a USIC channel operated in IIS mode.

Note: Operating Conditions apply.

Table 52 USIC IIS Master Transmitter Timing

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Clock period	t_1 CC	33.3	–	–	ns	
Clock high time	t_2 CC	0.35 x t_{1min}	–	–	ns	
Clock low time	t_3 CC	0.35 x t_{1min}	–	–	ns	
Hold time	t_4 CC	0	–	–	ns	
Clock rise time	t_5 CC	–	–	0.15 x t_{1min}	ns	

3.3.9 USB Interface Characteristics

The Universal Serial Bus (USB) Interface is compliant to the USB Rev. 2.0 Specification. High-Speed Mode is not supported.

Note: These parameters are not subject to production test, but verified by design and/or characterization.

Table 54 USB Timing Parameters (operating conditions apply)

Parameter	Symbol		Values			Unit	Note / Test Condition
			Min.	Typ.	Max.		
Rise time	t_R	CC	4	–	20	ns	C_L = 50 pF
Fall time	t_F	CC	4	–	20	ns	C_L = 50 pF
Rise/Fall time matching	t_R/t_F	CC	90	–	111.11	%	C_L = 50 pF
Crossover voltage	V_{CRS}	CC	1.3	–	2.0	V	C_L = 50 pF

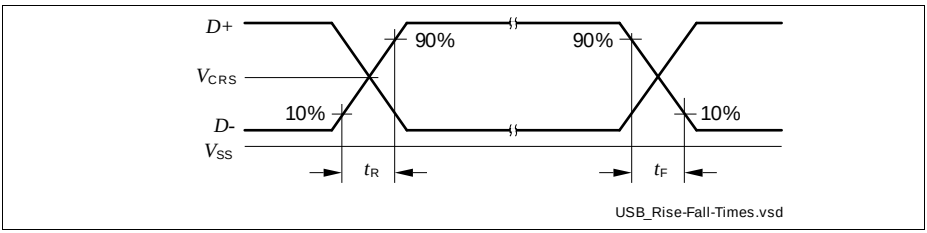

Figure 35 USB Signal Timing

power dissipation must be limited so that the average junction temperature does not exceed 150 °C.

The difference between junction temperature and ambient temperature is determined by
$\Delta T = (P_{INT} + P_{IOSTAT} + P_{IODYN}) \times R_{\Theta JA}$

The internal power consumption is defined as
$P_{INT} = V_{DDP} \times I_{DDP}$ (switching current and leakage current).

The static external power consumption caused by the output drivers is defined as
$P_{IOSTAT} = \Sigma((V_{DDP}-V_{OH}) \times I_{OH}) + \Sigma(V_{OL} \times I_{OL})$

The dynamic external power consumption caused by the output drivers (P_{IODYN}) depends on the capacitive load connected to the respective pins and their switching frequencies.

If the total power dissipation for a given system configuration exceeds the defined limit, countermeasures must be taken to ensure proper system operation:

- Reduce V_{DDP}, if possible in the system
- Reduce the system frequency
- Reduce the number of output pins
- Reduce the load on active output drivers

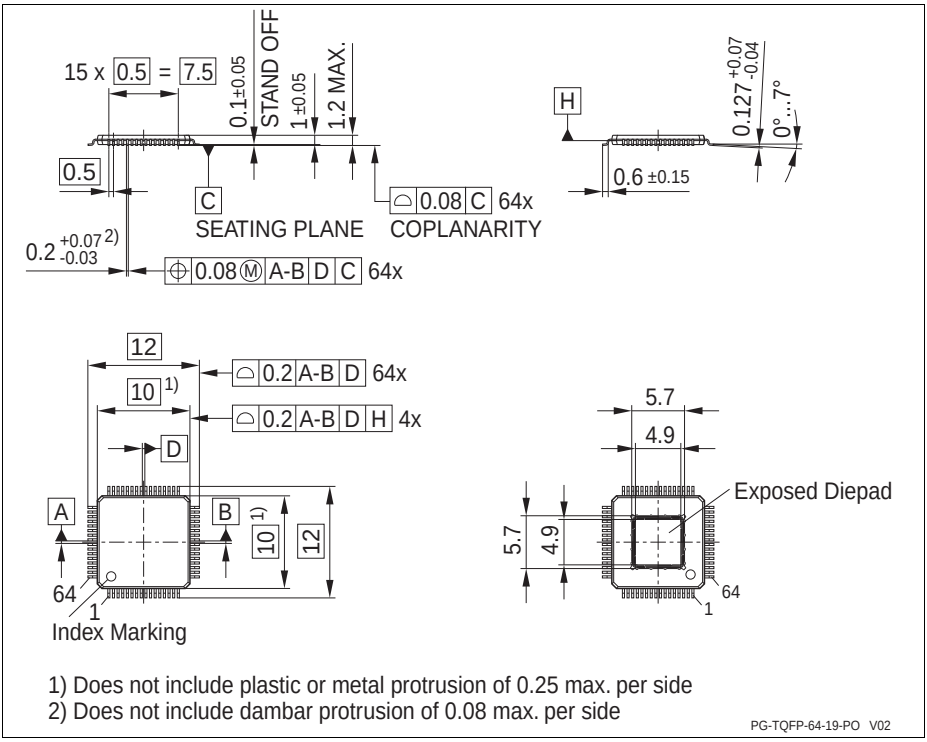

Figure 37 PG-TQFP-64-19 (Plastic Green Thin Profile Quad Flat Package)

Table 57 Differences PG-VQFN-48-53 to PG-VQFN-48-71

Change	PG-VQFN-48-53	PG-VQFN-48-71
Package corner	chamfered	right-angled
Lead width	$0.23^{\pm 0.05}$ mm	$0.25^{(+0.05, -0.07)}$ mm
Lead height	$0.4^{\pm 0.07}$ mm	$0.4^{\pm 0.05}$ mm

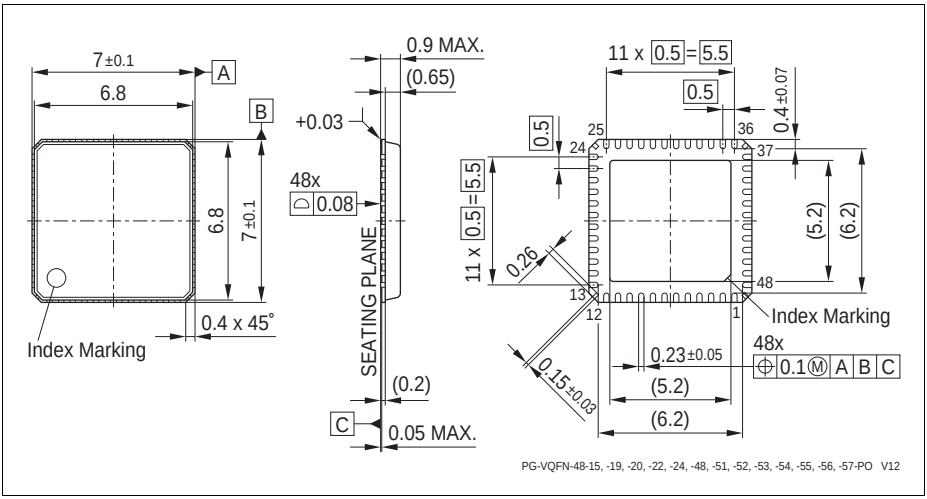

Figure 38 **PG-VQFN-48-53** (Plastic Green Very Thin Profile Flat Non Leaded Package)

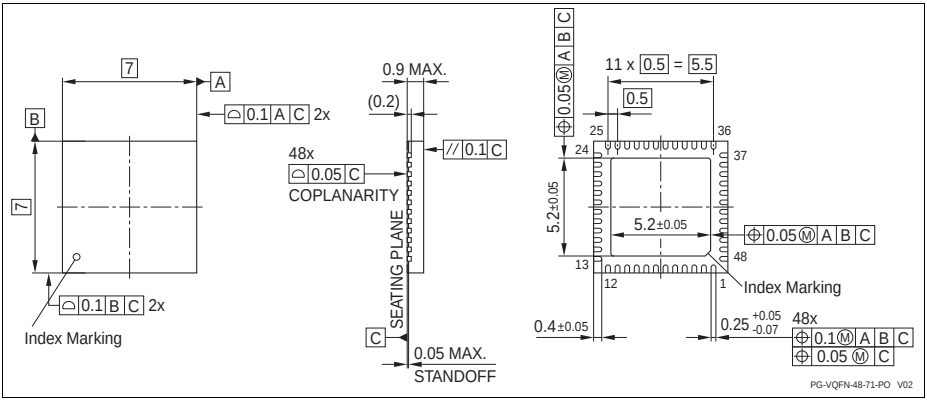

Figure 39 **PG-VQFN-48-71** (Plastic Green Very Thin Profile Flat Non Leaded Package)

All dimensions in mm.

You can find complete information about Infineon packages, packing and marking in our Infineon Internet Page “Packages”: **http://www.infineon.com/packages**